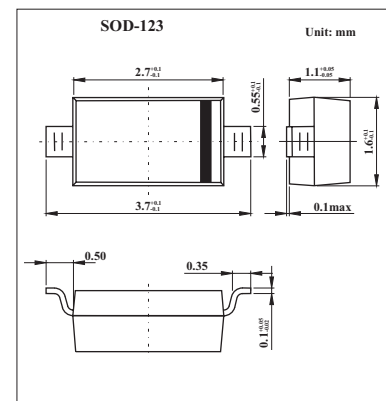


## Silicon Schottky Barrier Diode

## HSU88

## ■ Features

- Low capacitance. (C=0.8pF max)
- Low forward voltage.
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.



## ■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	10	V
Average rectified current	I <sub>O</sub>	15	mA
Junction temperature	T <sub>j</sub>	125	°C
Storage temperature	T <sub>stg</sub>	-55 to +125	°C

## ■ Electrical Characteristics Ta = 25 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 1 mA	350		420	mV
		I <sub>F</sub> = 10 mA	500		580	
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 2 V			0.2	μ A
		V <sub>R</sub> = 10 V			10	
Capacitance	C	V <sub>R</sub> = 0 V, f = 1 MHz			0.8	pF
ESD-Capability (Note 1)		C = 200pF, Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ; I<sub>R</sub> ≥ 400 nA at V<sub>R</sub> = 2 V

## ■ Marking

Marking	9
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